



IN THE UNITED STATES
PATENT AND TRADEMARK OFFICE

PATENT APPLICATION

Huili Shao
Allen Yen
Susan Clay Vitkavage

CASE 1-10-3

Serial No. 09/464811

Group Art Unit 2815

Filed December 17, 1999

Examiner L. Cruz

Title Integration Of Low Dielectric Material In Semiconductor Circuit Structures

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Enclosed is an amendment in the above-identified application.

NO ADDITIONAL FEE REQUIRED

In the event of non-payment or improper payment of a required fee, the Commissioner is authorized to charge or to credit **Deposit Account No. 12-2325** as required to correct the error.

Respectfully,

Anthony Grillo, Attorney
Reg. No. 36535
610-712-3766.

Date:

10/17/00

Lucent Technologies Inc.
600 Mountain Avenue (Room 3C-512)
P.O. Box 636
Murray Hill, New Jersey 07974-0636

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to:
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Date



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AMENDMENT

In response to the Office Action mailed May 17, 2000, please amend the above-identified application as follows:

IN THE SPECIFICATION

- ✓ Page 7, line 31: change "2500" to -- 250 --.
- ✓ Page 8, line 19: after "dielectric layer" delete "350".

IN THE CLAIMS

a¹
1(Amended). A semiconductor structure comprising:
a first upper level of interconnect members formed over a semiconductor layer
having an electronic device formed thereon;
at least one lower level of interconnect members formed between the
semiconductor layer and the first upper level;

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